

P-Channel 30 V (D-S) MOSFET

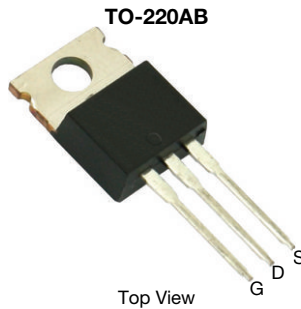
PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω) MAX.	I _D (A) ^d	Q _g (TYP.)
-30	0.0087 at V _{GS} = -10 V	-45	60
	0.0150 at V _{GS} = -4.5 V	-45	

FEATURES

- TrenchFET[®] power MOSFET
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

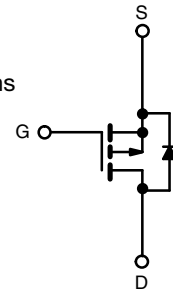


RoHS
COMPLIANT
HALOGEN
FREE



APPLICATIONS

- Power switch
- Load switch in high current applications
- DC/DC converters



P-Channel MOSFET

Ordering Information:

SUP45P03-09-GE3 (lead (Pb)-free and halogen-free)

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DS}	-30	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 150 °C) ^d	I _D	T _C = 25 °C	A
		T _C = 70 °C	
Pulsed Drain Current (t = 100 μs)	I _{DM}	-100	A
Avalanche Current	I _{AS}	-35	
Single Avalanche Energy ^a	E _{AS}	61	mJ
Maximum Power Dissipation ^a	P _D	T _C = 25 °C	73.5 ^b
		T _A = 25 °C ^c	3.1
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	40	°C/W
Junction-to-Case (Drain)	R _{thJC}	1.7	

Notes

- Duty cycle ≤ 1 %.
- See SOA curve for voltage derating.
- When mounted on 1" square PCB (FR4 material).
- Package limited.



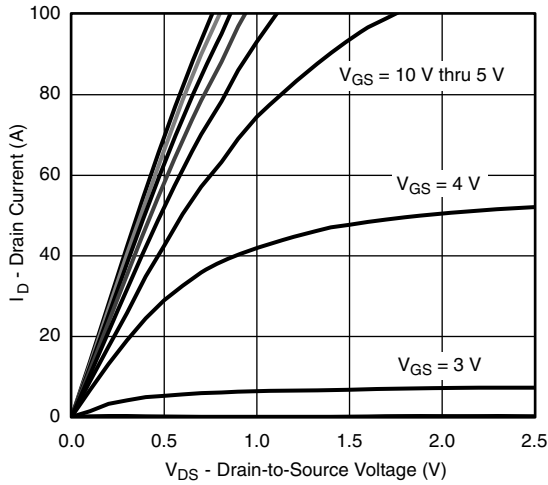
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = -250\text{ }\mu\text{A}$	-30	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\text{ }\mu\text{A}$	-1	-	-2.5	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$	-	-	± 250	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30\text{ V}$, $V_{GS} = 0\text{ V}$	-	-	-1	μA
		$V_{DS} = -30\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$	-	-	-50	
		$V_{DS} = -30\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$	-	-	-250	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq -10\text{ V}$, $V_{GS} = -10\text{ V}$	-50	-	-	A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}$, $I_D = -20\text{ A}$	-	0.0072	0.0087	Ω
		$V_{GS} = -4.5\text{ V}$, $I_D = -15\text{ A}$	-	0.0125	0.0150	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15\text{ V}$, $I_D = -20\text{ A}$	-	45	-	S
Dynamic ^b						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = -15\text{ V}$, $f = 1\text{ MHz}$	-	2700	-	μF
Output Capacitance	C_{oss}		-	515	-	
Reverse Transfer Capacitance	C_{rss}		-	445	-	
Total Gate Charge ^c	Q_g	$V_{DS} = -15\text{ V}$, $V_{GS} = -10\text{ V}$, $I_D = -20\text{ A}$	-	60	90	nC
Gate-Source Charge ^c	Q_{gs}		-	9.3	-	
Gate-Drain Charge ^c	Q_{gd}		-	15	-	
Gate Resistance	R_g	$f = 1\text{ MHz}$	0.5	2.5	5	Ω
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = -15\text{ V}$, $R_L = 1.5\text{ }\Omega$ $I_D \cong -10\text{ A}$, $V_{GEN} = -10\text{ V}$, $R_g = 1\text{ }\Omega$	-	12	20	ns
Rise Time ^c	t_r		-	11	20	
Turn-Off Delay Time ^c	$t_{d(off)}$		-	40	60	
Fall Time ^c	t_f		-	12	20	
Drain-Source Body Diode Ratings and Characteristics ^b ($T_C = 25\text{ }^\circ\text{C}$)						
Continuous Current	I_S		-	-	-45	A
Pulsed Current ($t = 100\text{ }\mu\text{s}$)	I_{SM}		-	-	-100	
Forward Voltage ^a	V_{SD}	$I_F = -10\text{ A}$, $V_{GS} = 0\text{ V}$	-	-0.8	-1.5	V
Reverse Recovery Time	t_{rr}	$I_F = -10\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	-	27	40	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$		-	1.3	2	A
Reverse Recovery Charge	Q_{rr}		-	20	30	nC

Notes

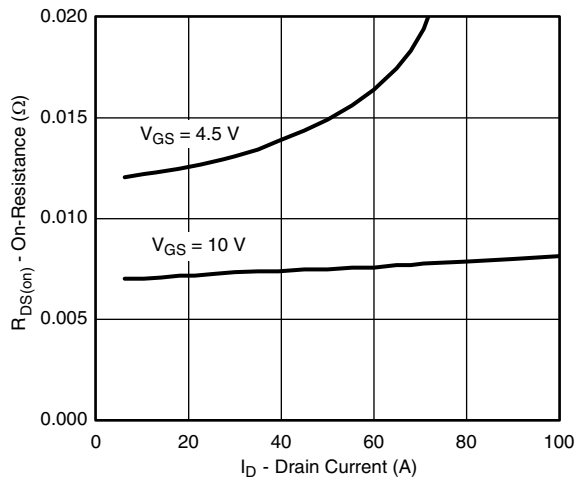
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

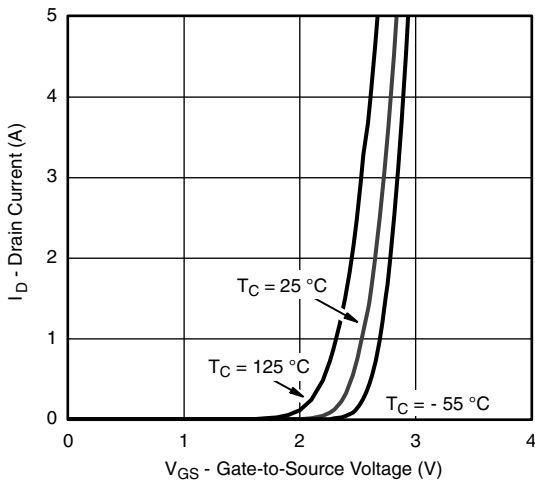
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



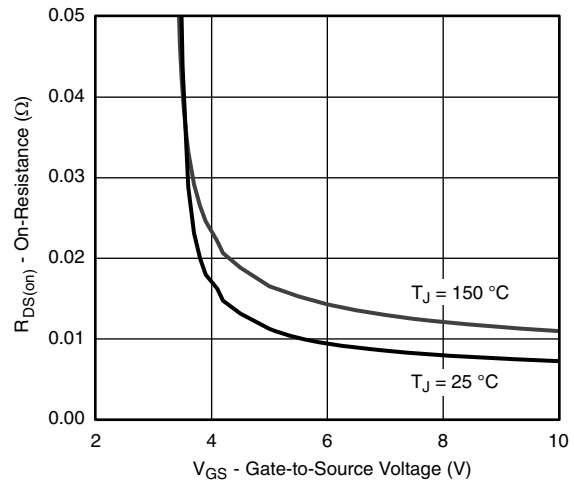
Output Characteristics



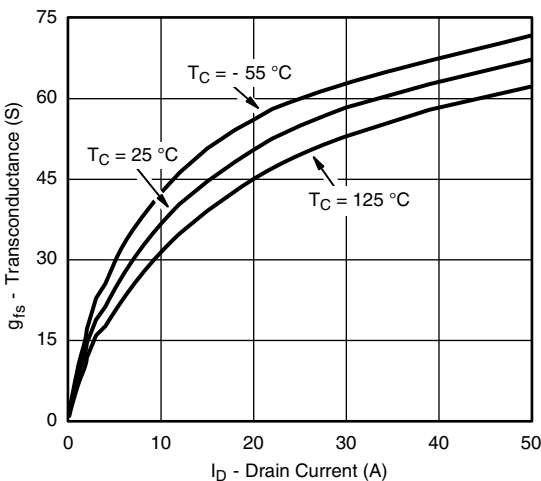
On-Resistance vs. Drain Current



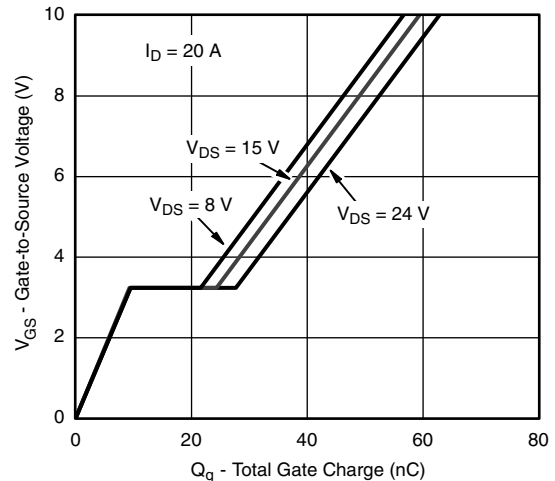
Transfer Characteristic



On-Resistance vs. Gate-to-Source Voltage



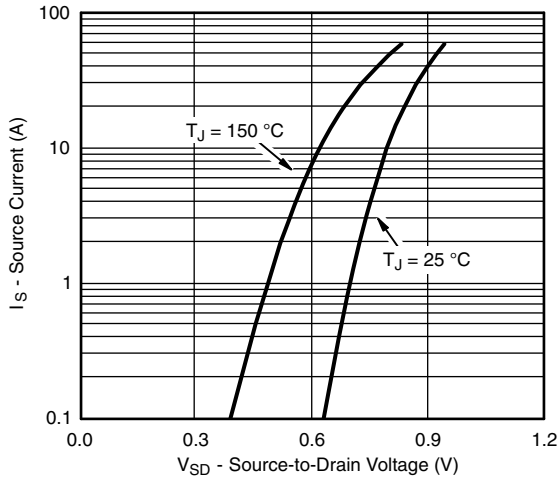
Transconductance



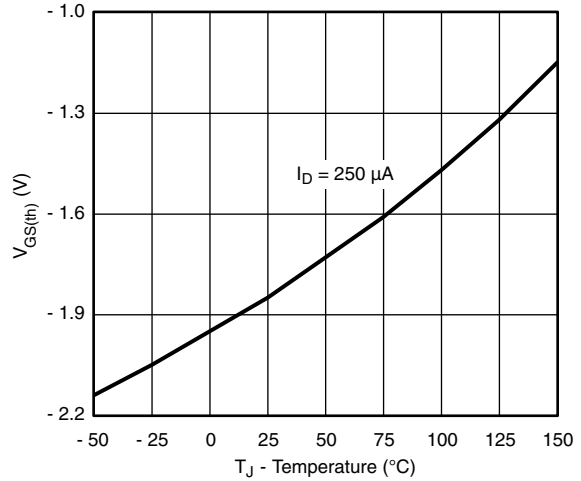
Gate Charge



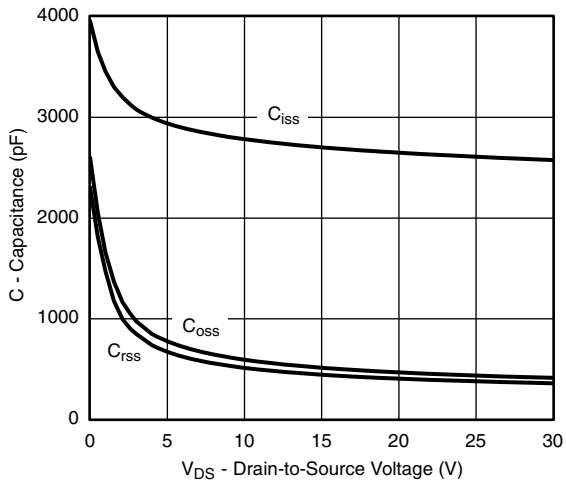
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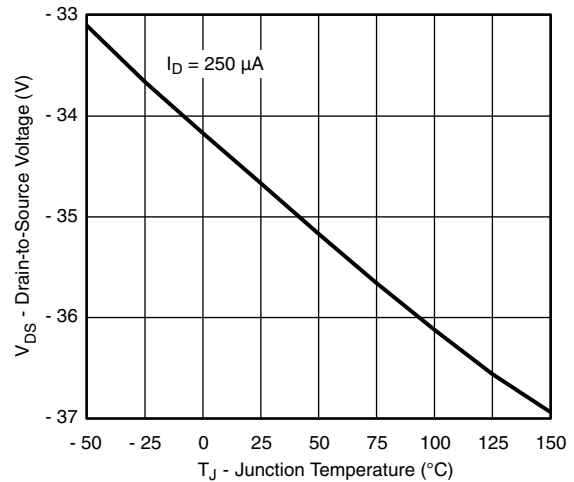
Source-Drain Diode Forward Voltage



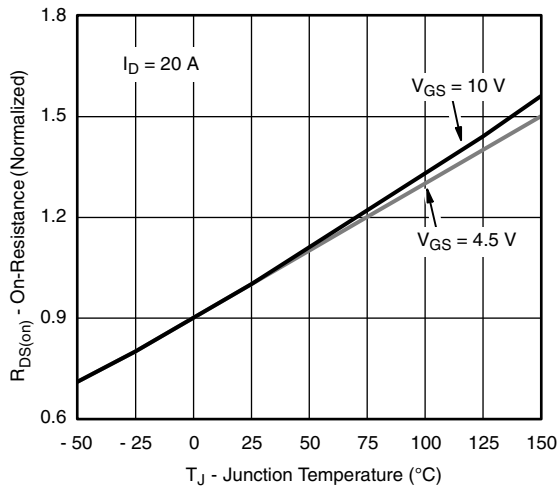
Threshold Voltage



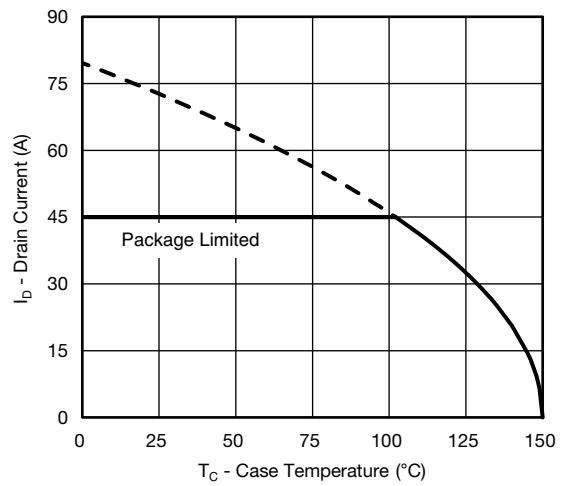
Capacitance



Drain Source Breakdown vs. Junction Temperature



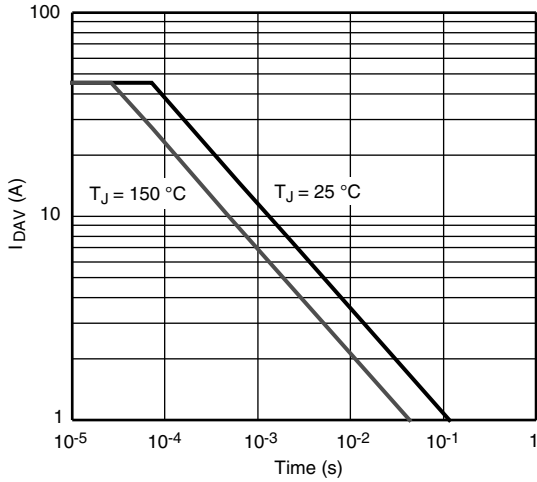
On-Resistance vs. Junction Temperature



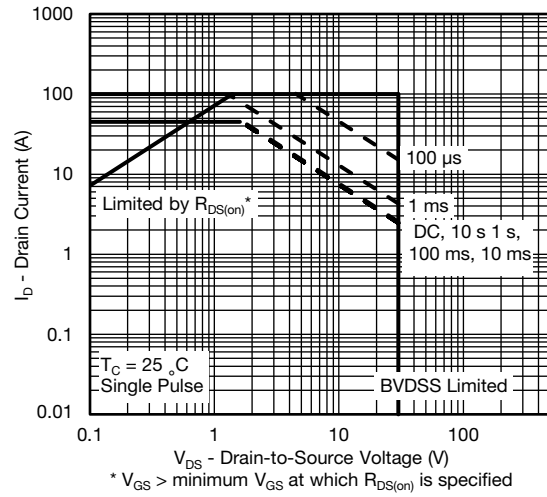
Current Derating



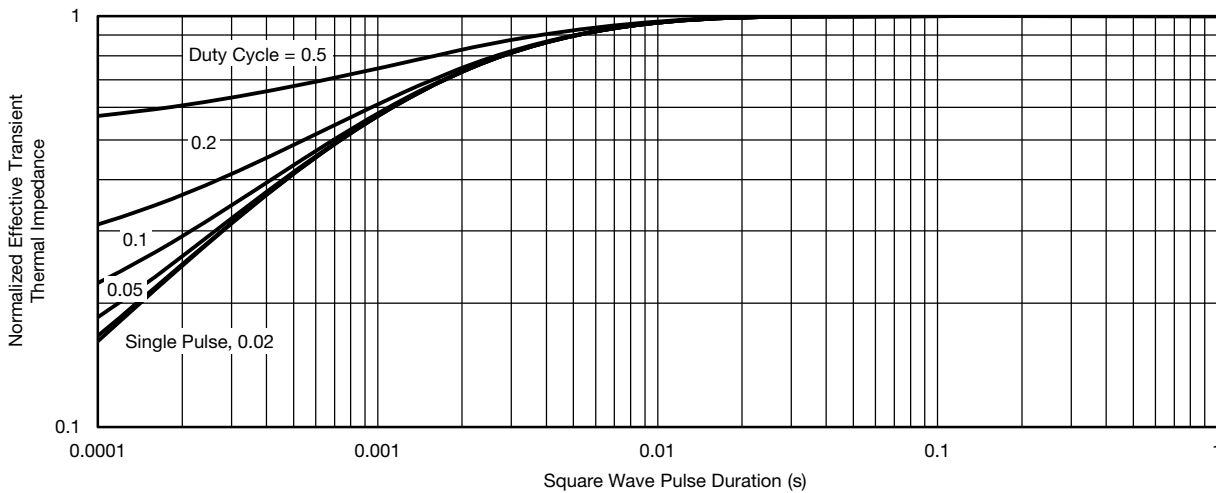
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Single Pulse Avalanche Current Capability vs. Time



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

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TO-220AB

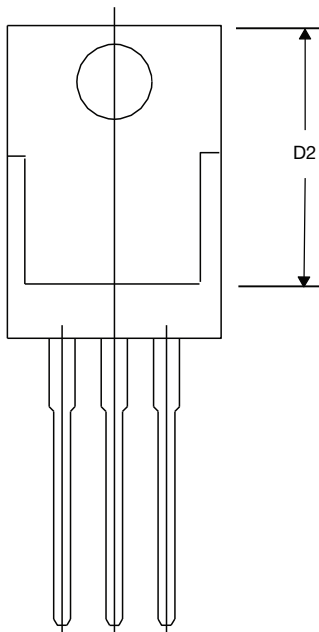


DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
D2	12.19	12.70	0.480	0.500
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
$\varnothing P$	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118

ECN: T14-0413-Rev. P, 16-Jun-14
DWG: 5471

Note

* M = 1.32 mm to 1.62 mm (dimension including protrusion)
Heatsink hole for HVM





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